Session: TH1E

Linear Device Modeling

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Linear device model extraction is a critical procedure for the development of low frequency and microwave/millimeter wave noise models. In this session, new results are presented for: the development of 1/f noise models for HBTs and the development of accurate FET models including parasitic extraction, microwave/millimeter wave noise models and the temperature dependence of noise models.

8:00 am - 9:50 am Thursday, June 20, 1996
Room 130